



EpiGaN Receives Official Certification of Compliance to ISO9001:2015.

Hasselt, Belgium, 24 June 2016 --- EpiGaN, the leading European supplier of commercial-grade 150mm- and 200mm- GaN-on-Silicon epiwafers, announces that the production facility at its headquarters in Hasselt, Belgium, is now fully certified to the quality management system ISO9001:2015. The official notification from the International Organization for Standardization was received on June 7, 2016.

EpiGaN, operating out of Hasselt, Belgium, is a key global player in developing III/V materials and delivering GaN-on-Si and GaN-on-SiC epi-wafers to semiconductor manufacturers worldwide. EpiGaN's product portfolio covers state-of-the-art solutions for power switching as well as RF millimeter-wave power and sensor applications. EpiGaN is producing GaN structures on Si substrates up to 200mm diameter at the 600V node to enable its customers to successfully position themselves in rapidly growing market segments.

"The official ISO9001:2015 certification is very important to us," notes EpiGaN cofounder and CEO Dr Marianne Germain. "It reassures our commercial customers and institutional program partners on a global scale of our unwavering commitment to the professional quality management of our wafer deliveries. It proves that EpiGaN is a well established entity in its field. There are not many organizations that are certified to the new updated version of the standard."

The full range of quality management measures according to ISO9001 has been in place internally at EpiGaN's Hasselt campus since 2012. "The EpiGaN quality management system has grown up together with the company: all the prescribed standardization procedures had been installed, documented and maintained according to the ISO9001 requirements," reports Domenica Visalli, Ph.D., GaN Project Engineer and Quality Manager at EpiGaN. "The formal application procedure for ISO9001:2015 was launched in January 2016 and we received the final notification within the usual time frame on June 7, 2016."

EpiGaN was founded in 2010 by Drs Marianne Germain (CEO), Joff Derluyn (CTO) and Stefan Degroote (COO), as a spin-off from renowned Belgian micro- and nano-electronics research center Imec. Since then, EpiGaN has become a key player in GaN-on-Si and GaN-on-SiC semiconductors. In 2011, the company was joined by the start-up investment firms Robert Bosch Venture Capital, Capricorn CleanTech Fund and LRM to enable the installation of its state-of-the-art wafer production facility. In June the Beijing/Brussels-based Euro-Asia private equity fund A Capital has joined the initial investors in EpiGaN to fund the company's expansion of its sales and support base to Asian markets. EpiGaN is doing volume production and wafer characterization at its Belgian

headquarters, the Research Campus Hasselt, located in the European high-tech triangle Eindhoven-Leuven-Aachen.

In January 2016, EpiGaN signed a global representation agreement for its 150mm and 200mm GaN on Si power semiconductor product solutions with SunEdison Semiconductor, a leading US manufacturer of Si substrates for semiconductor manufacturing based in St. Peters, MO, USA.

About EpiGaN

Founded in 2010, EpiGaN provides industry-leading III-nitride epitaxial material solutions for top-performance devices, offering device manufacturers early access to a unique and proven GaN/Si and GaN/SiC technology for next-generation power switching and RF devices with significantly improved RF loss performance, as well as advanced sensor device solutions. Key applications for EpiGaN's technology solutions are consumer power supplies, drives for electrical motors, UPS systems, hybrid electric vehicles, solar inverters, RF power amplifiers for 4/5G mobile broadband, CATV and bio/chem. sensor devices. Lou Hermans, a founder of CMOSIS, is Chairman of the Board of Directors of EpiGaN. More information: www.epigan.com

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